

11A, 500V N-CHANNEL POWER MOSFET

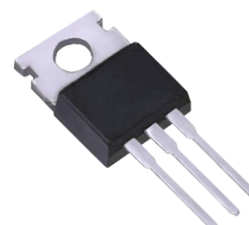
■ DESCRIPTION

The **UTC 11N50** is an N-channel enhancement mode power MOSFET. It uses UTC advanced planar stripe, DMOS technology to provide customers perfect switching performance, minimal on-state resistance. It also can withstand high energy pulse in the avalanche and commutation mode.

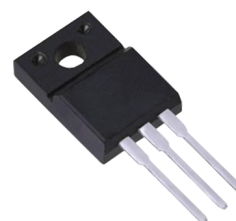
The **UTC 11N50** is universally applied in electronic lamp ballasts based on half bridge topology, high efficiency switched mode power supplies, active power factor correction, etc.

■ FEATURES

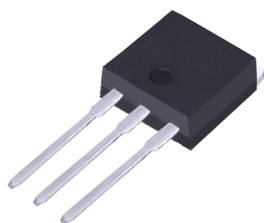
- * $R_{DS(ON)}=0.55\Omega @ V_{GS}=10V$
- * Fast Switching
- * With 100% Avalanche Tested



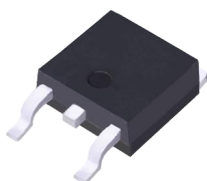
TO-220



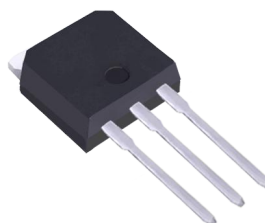
TO-220F



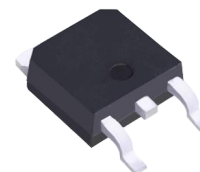
TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V_{DSS}	500	V
Gate to Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	11 (Note 2)	A
	$T_C=100^\circ\text{C}$		7 (Note 2)	A
Pulsed Drain Current (Note 3)		I_{DM}	44 (Note 2)	A
Single Pulsed Avalanche Energy(Note 4)		E_{AS}	670	mJ
Peak Diode Recovery dv/dt (Note 5)		dv/dt	4.5	V/ns
Power Dissipation	$T_C=25^\circ\text{C}$	TO-220	195	W
		TO-220F1	40	
		TO-220F	48	
		TO-262	195	
	Derate above 25°C	TO-220	1.56	W/ $^\circ\text{C}$
		TO-220F1	0.32	
		TO-220F	0.39	
		TO-262	1.56	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature
3. Repetitive Rating : Pulse width limited by maximum junction temperature
4. $L=10\text{mH}$, $I_{AS}=11\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
5. $I_{SD}\leq 11\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.64	$^\circ\text{C}/\text{W}$
	TO-220F1		3.1	
	TO-220F		2.58	
	TO-262		0.64	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	500			V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.5		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
		V _{DS} =500V, T _J =125°C			100	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.5A		0.48	0.55	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		1515	2055	pF
Output Capacitance	C _{OSS}			185	235	pF
Reverse Transfer Capacitance	C _{RSS}			25	30	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =400V, V _{GS} =10V, I _D =11A (Note 1, 2)		43	55	nC
Gate-Source Charge	Q _{GS}			8		nC
Gate-Drain Charge	Q _{GD}			19		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =250V, I _D =11A, R _G =3Ω (Note 1, 2)		24	57	ns
Turn-ON Rise Time	t _R			70	150	ns
Turn-OFF Delay Time	t _{D(OFF)}			120	250	ns
Turn-OFF Fall Time	t _F			75	160	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				11	A
Maximum Body-Diode Pulsed Current	I _{SM}				44	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =11A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =11A, dI _F /dt=100A/μs (Note 1)		90		ns
Body Diode Reverse Recovery Charge	Q _{RR}				1.5	

Note: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature